

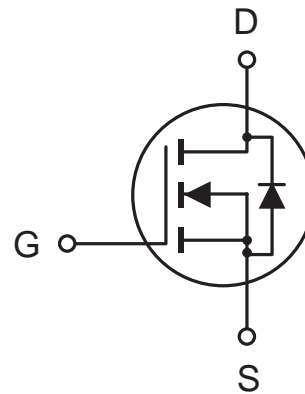
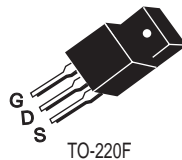
CEF08N2

Nov. 2002

N-Channel Logic Level Enhancement Mode Field Effect Transistor

FEATURES

- 250V, 6A, $R_{DS(ON)}=450m\Omega$ @ $V_{GS}=10V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- TO-220F full-pak for through hole



ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|-----------------------------------|------------|------|
| Drain-Source Voltage | V _{DS} | 250 | V |
| Gate-Source Voltage | V _{GS} | ± 30 | V |
| Drain Current-Continuous -Pulsed | I _D | 6 | A |
| | I _{DM} | 24 | A |
| Drain-Source Diode Forward Current | I _S | 6 | A |
| Maximum Power Dissipation @ $T_c=25^\circ\text{C}$ Derate above 25°C | P _D | 38 | W |
| | | 0.3 | W/°C |
| Operating and Storage Temperature Range | T _J , T _{STG} | -50 to 150 | °C |

THERMAL CHARACTERISTICS

| | | | |
|---|-----------------|-----|------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 3.3 | °C/W |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 65 | °C/W |

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ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|--|---------------------|---|-----|-----|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} = 0V, I _D = 250μA | 250 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 250V, V _{GS} = 0V | | | 25 | μA |
| Gate-Body Leakage | I _{GSS} | V _{GS} = ±30V, V _{DS} = 0V | | | ±100 | nA |
| ON CHARACTERISTICS^a | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250μA | 2 | | 4 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} = 10V, I _D = 5.1A | | | 450 | mΩ |
| On-State Drain Current | I _{D(ON)} | V _{GS} = 10V, V _{DS} = 10V | 10 | | | A |
| Forward Transconductance | g _{FS} | V _{DS} = 50V, I _D = 5.1A | | 4.4 | | S |
| DYNAMIC CHARACTERISTICS^b | | | | | | |
| Input Capacitance | C _{ISS} | V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz | | 630 | | pF |
| Output Capacitance | C _{OSS} | | | 100 | | pF |
| Reverse Transfer Capacitance | C _{RSS} | | | 40 | | pF |
| SWITCHING CHARACTERISTICS^b | | | | | | |
| Turn-On Delay Time | t _{D(ON)} | V _{DD} = 125V, I _D = 5.6A, V _{GS} = 10V, R _{GEN} = 12Ω | | 19 | 40 | ns |
| Rise Time | t _r | | | 11 | 30 | ns |
| Turn-Off Delay Time | t _{D(OFF)} | | | 46 | 90 | ns |
| Fall Time | t _f | | | 10 | 30 | ns |
| Total Gate Charge | Q _g | V _{DS} = 200V, I _D = 5.6A, V _{GS} = 10V | | 26 | 33 | nC |
| Gate-Source Charge | Q _{gs} | | | 5 | | nC |
| Gate-Drain Charge | Q _{gd} | | | 11 | | nC |

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ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|----------|---------------------------|-----|-----|-----|------|
| DRAIN-SOURCE DIODE CHARACTERISTICS^a | | | | | | |
| Diode Forward Voltage | V_{SD} | $V_{GS} = 0V, I_s = 8.1A$ | | 0.9 | 1.5 | V |

Notes

- a. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

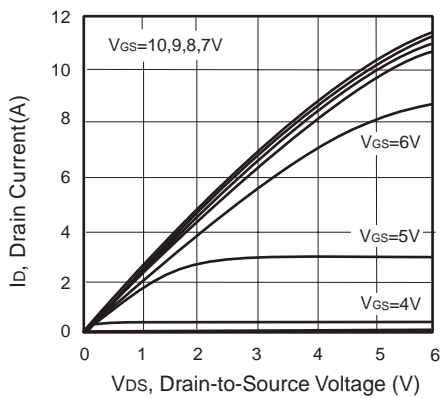


Figure 1. Output Characteristics

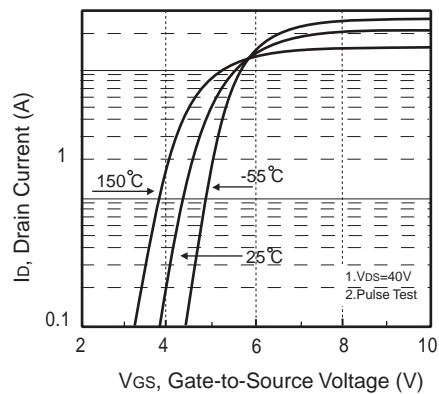


Figure 2. Transfer Characteristics

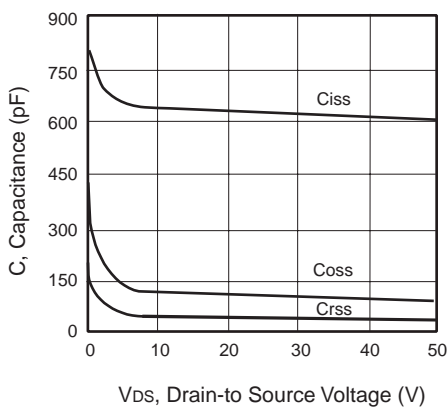


Figure 3. Capacitance

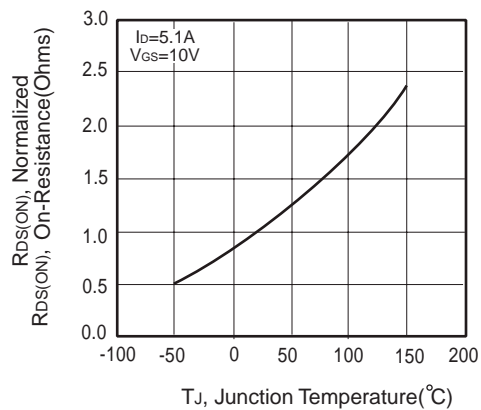


Figure 4. On-Resistance Variation with Temperature

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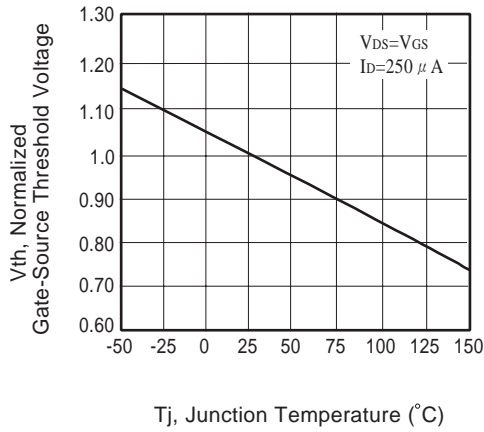


Figure 5. Gate Threshold Variation with Temperature

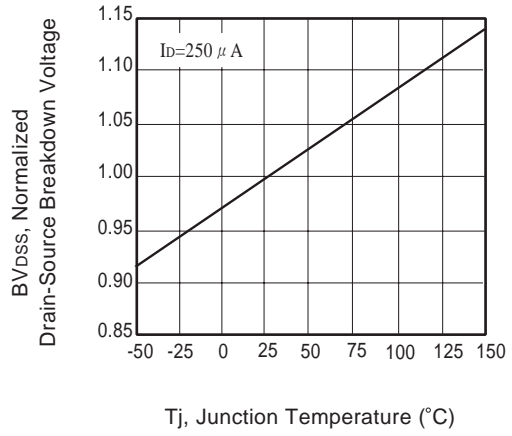


Figure 6. Breakdown Voltage Variation with Temperature

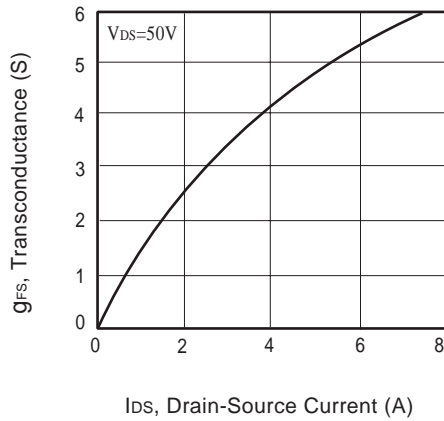


Figure 7. Transconductance Variation with Drain Current

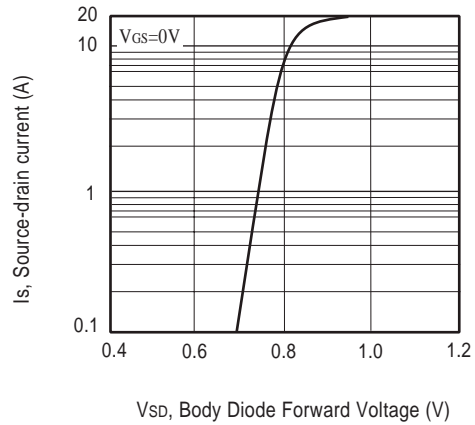


Figure 8. Body Diode Forward Voltage Variation with Source Current

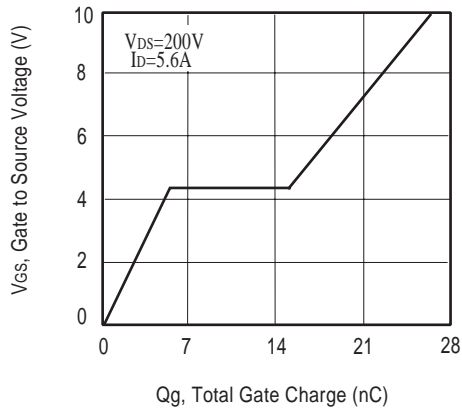


Figure 9. Gate Charge

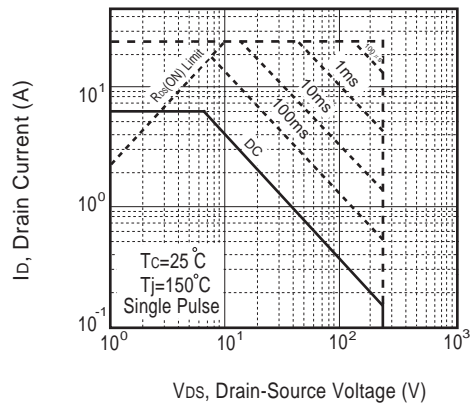


Figure 10. Maximum Safe Operating Area

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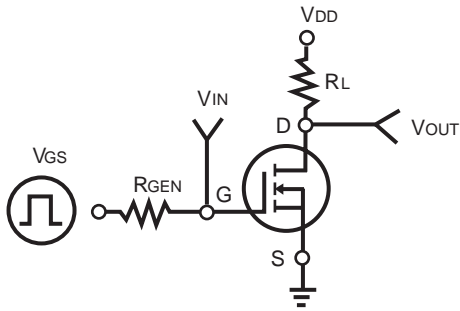


Figure 11. Switching Test Circuit

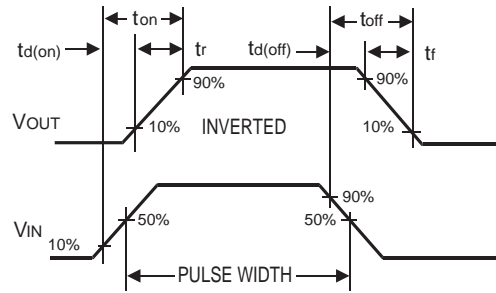


Figure 12. Switching Waveforms

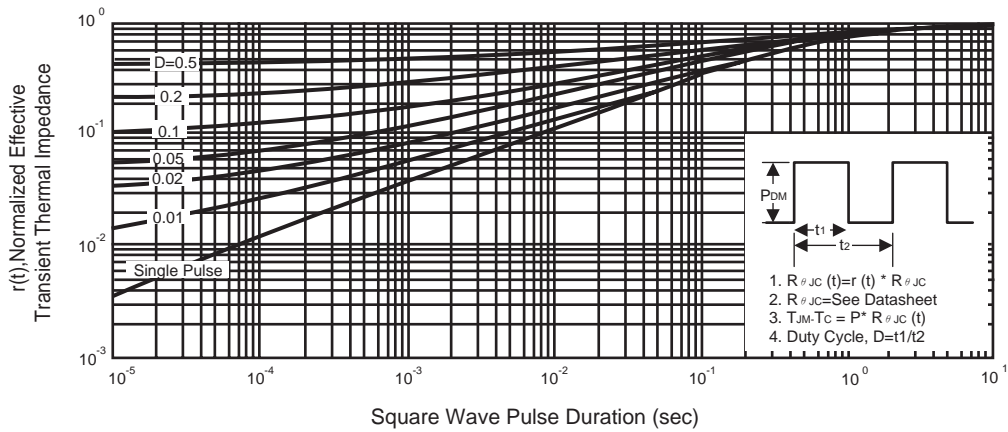


Figure 13. Normalized Thermal Transient Impedance Curve